

Taiwan Semiconductor

Dual N-Channel MOSFET

 $30V, 20A, 20m\Omega$

FEATURES

EMICONDUCTOR

AIWAN

- Fast switching
- 100% avalanche tested
- Pb-free plating
- RoHS compliant
- Halogen-free package

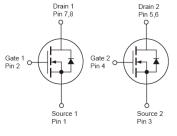
APPLICATION

- Power Supply
- Motor COntrol

KEY PERFORMANCE PARAMETERS					
PARAM	METER	VALUE	UNIT		
V	V _{DS}		V		
D (max)	V _{GS} = -10V	20			
$R_{DS(on)}$ (max)	V _{GS} = -4.5V	30	mΩ		
Qg		4.1	nC		







Dual N-Channel MOSFET

Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	30	V		
Gate-Source Voltage		V _{GS}	±20	V		
Continuous Drain Current (Note 1)	$T_c = 25^{\circ}C$	- I _D	20	•		
Continuous Drain Current	T _C = 100°C		13	A		
Pulsed Drain Current (Note 2)		I _{DM}	80	А		
Total Power Dissipation @ $T_c = 25^{\circ}C$		P _{DTOT}	20	W		
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	14	mJ		
Single Pulsed Avalanche Current (Note 3)		I _{AS}	17	А		
Operating Junction and Storage Temperatur	re Range	T _J , T _{STG}	- 55 to +150	°C		

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	6.4	°C/W		
Junction to Ambient Thermal Resistance	R _{eja}	62	°C/W		

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air

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PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)			1			I
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1.2	1.5	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
7 0 4 14 5 4 0 4	$V_{DS} = 30V, V_{GS} = 0V$	_			1	μA
Zero Gate Voltage Drain Current	V _{DS} = 24V, Tc = 125°C	I _{DSS}			10	
	$V_{GS} = 10V, I_D = 10A$	_		17	20	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_{D} = 6A$	$R_{DS(on)}$		23	30	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 6A$	g _{fs}		13		S
Dynamic (Note 5)						•
Total Gate Charge		Q _g		4.1		
Gate-Source Charge	$V_{DS} = 15V, I_D = 8A,$	Q _{gs}		1		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		2.1		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{iss}		345		
Output Capacitance		C _{oss}		55		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		32		
Switching (Note 6)						•
Turn-On Delay Time		t _{d(on)}		2.8		
Turn-On Rise Time	$V_{DD} = 15V, I_D = 1A,$ $R_{GEN} = 6\Omega$	t _r		7.2		
Turn-Off Delay Time		t _{d(off)}		15.8		ns
Turn-Off Fall Time		t _f		4.6		
Source-Drain Diode (Note 4)						•
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I _S			20	A
Maximum Pulse Drain-Source Diode Forward Current		I _{SM}			80	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V _{SD}			1	V

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 0.1mH, I_{AS} = 17A, V_{DD} = 25V, R_G = 25\Omega, Starting T_J = 25 ^{o}C

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM200N03DPQ33 RGG	PDFN33	5Kpcs / 13"Reel

Note:

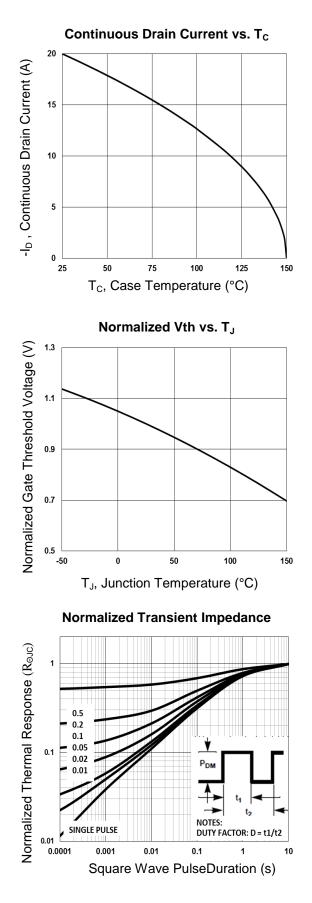
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

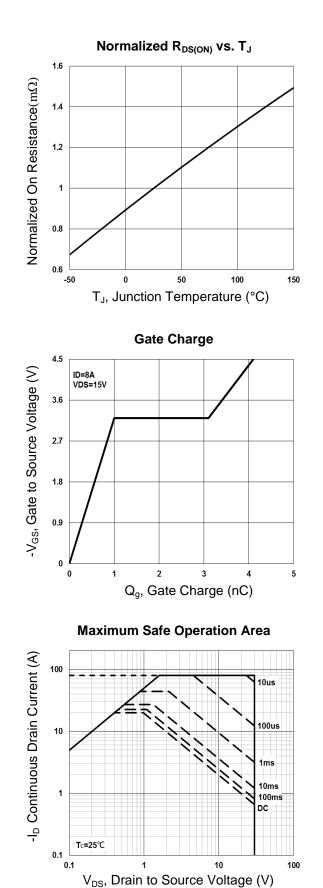
2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

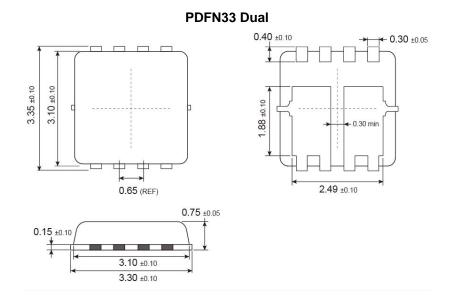




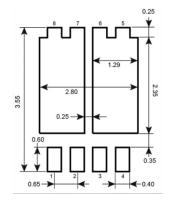




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM

C	200N03D YML	ו
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Y = Year Code

M = Month Code for Halogen Free Product O =Jan P =Feb Q =Mar R =Apr

- S = May T = Jun U = Jul V = Aug
- W =Sep X =Oct Y =Nov Z =Dec
- L = Lot Code (1~9, A~Z)



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